

Welcome to
7718 semester 1 2022
Mixed Signal Electronic Circuits

Instructor: Dr. Miki Moyal



Lectures

<http://www.gigalogchip.com/lectures.html>

Lecture 4

Sample (Track) and Hold

Agenda

Part I : SAMPLING SAMPLE AND HOLD

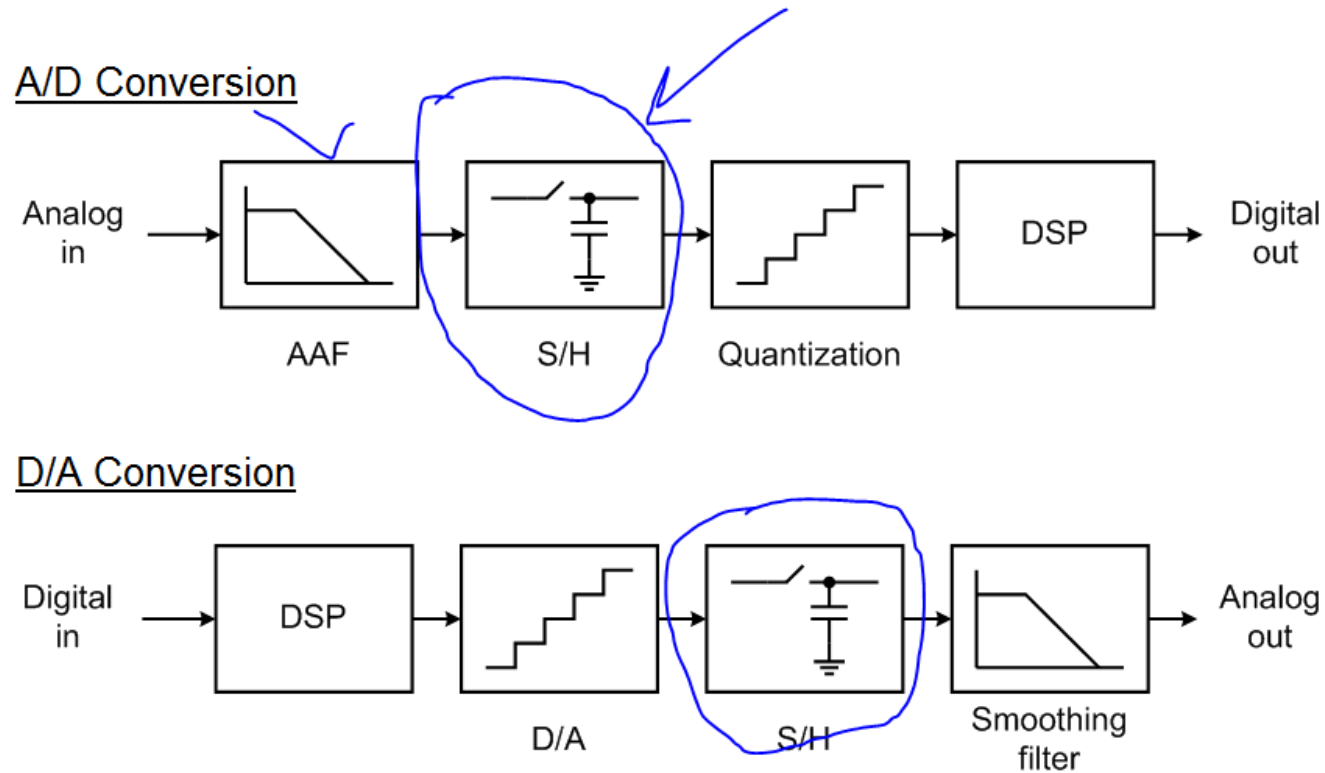
Part II : THE MOS SWITCH

Part III: S/H DISTORTION

Part IV: S/H CIRCUITS

Part V: S/H ACCOMPANYING BUFFERS

A/D and D/A Conversion



Why we need it

Some ADCs cant do without it

But

In high speed/accuracy it's the limiting elements in ADCs

It's the source of KT/C Noise and Harmonics

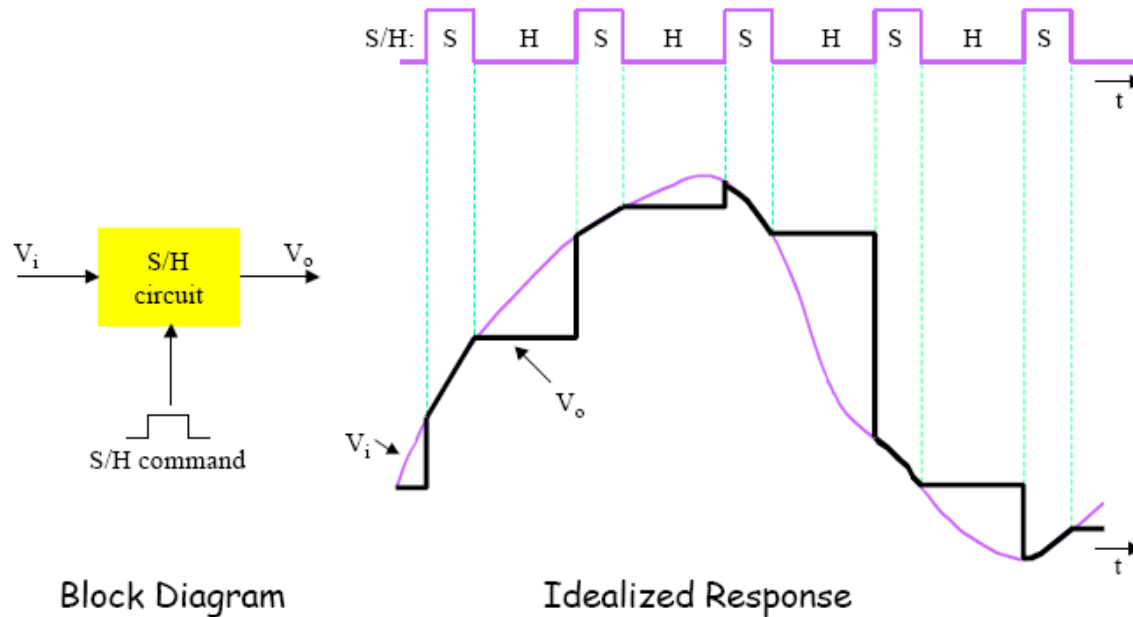
It's one more source effected by clock jitter input

It's the source of Power consumption (maybe the highest)

Part I : SAMPLING WITH SAMPLE AND HOLD SAMPLE/Trach AND HOLD –OPERATION

Sample-and-Hold Circuit

What does Track/Hold Look like ?



Source: Analog MS centre TAMU

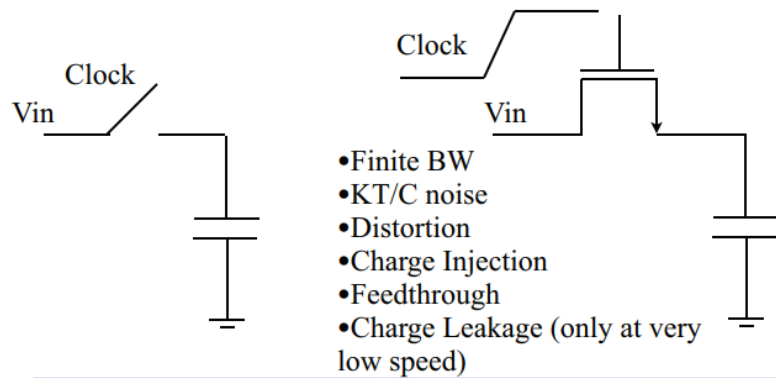
SAMPLING:

The Sample and hold keeps the Analog value fixed for a clock duration.

The MOS switch how to minimize error?

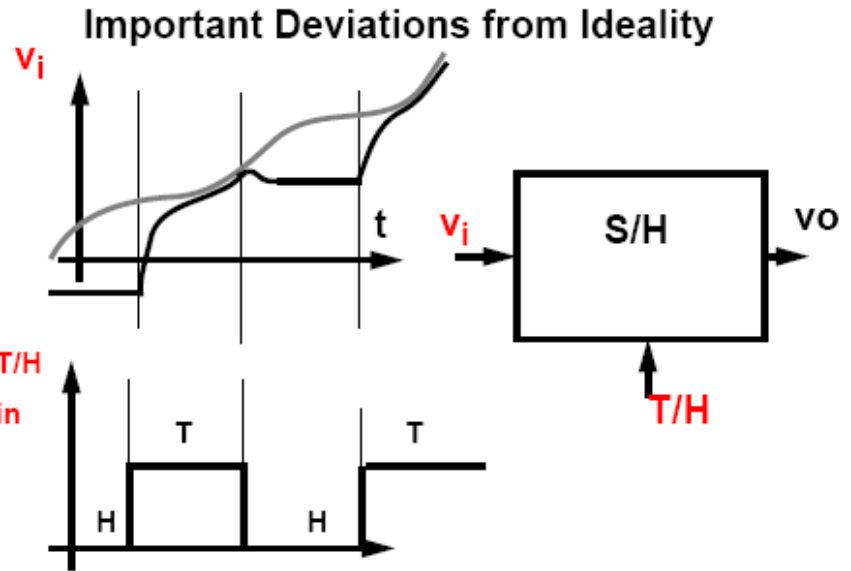
Ideal VS Real S/H

• Impulse-train sampling

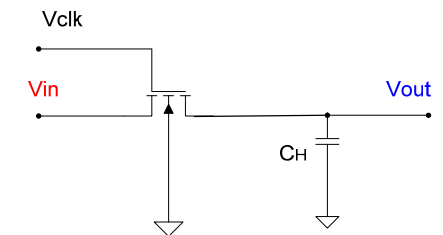


EECS 240 Topic 16: Offset Cancellation

© 2011 S.Gambini



1. Hold to Track Transition
Finite acquisition time
2. Track Mode
DC offset
Finite Bandwidth
3. Track-Hold Transition
S/H Offset
Aperture Delay
Aperture Jitter
4. Hold Mode
Droop



fundamental performance limits

Frequency domain transfer function

Sample Jitter and clock jitter

Acquisition Time, Sample BW

Droop and Feed through

KT/C noise

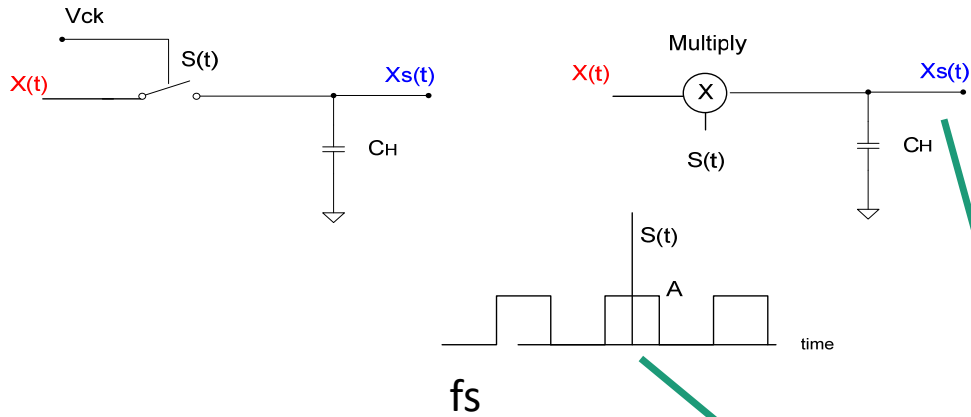
Linearity Real Performance limits- distortions

Charge Injections

Apparatus time

PSRR

Fourier transform of S/H system Sampling- Basics




$$C_x(n\omega_0) = \frac{1}{T_0} \int_{-\tau/2}^{\tau/2} s(t) e^{-jn\omega_0 t} dt$$

$$\rightarrow |C_x(n\omega_0)| = \frac{1}{T_0} \int A e^{-jn\omega_0 t} dt = A \omega_0 \tau \frac{\sin(\pi n \omega_0 \tau)}{\pi n \omega_0 \tau}$$

Do fft only on the hold area for tau length or on the tau section ..?

Vck is a clock at rate f_0 , f_s

More details proof on lect. adc



$$s(t) = C_0 + \sum_{n=1}^{\infty} 2C_n \cos(n\omega_0 t)$$

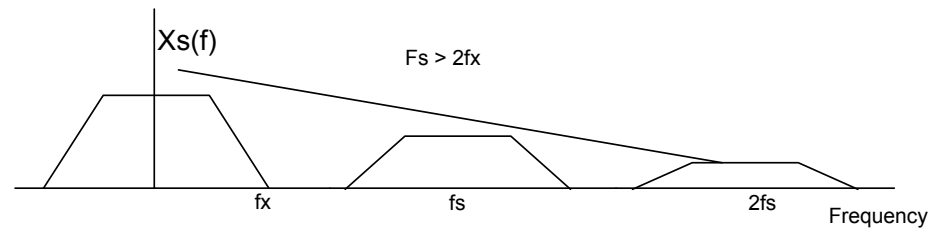
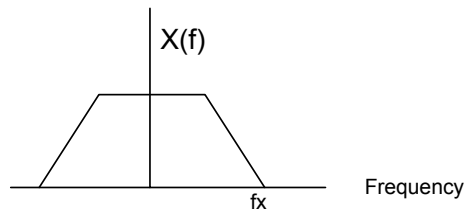
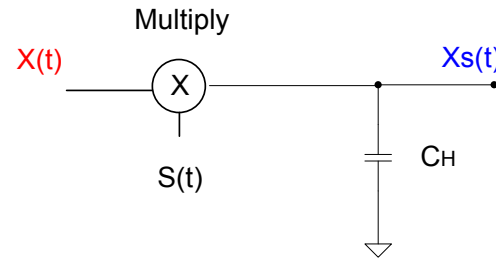
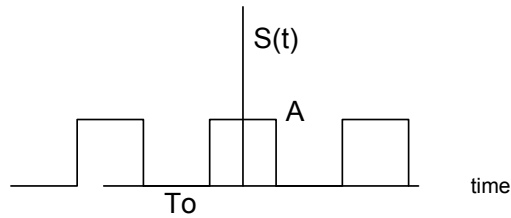
$$C_0 = \tau/T_0$$

$$C_n = A \omega_0 \tau \frac{\sin(\pi n \omega_0 \tau)}{\pi n \omega_0 \tau}$$

$$X_s(t) = s(t) \cdot X(t) = C_0 X(t) + 2C_1 X(t) \cdot \cos(\omega_s t) + 2C_2 X(t) \cos(2\omega_s t)$$

$$= C_0 X(f) + C_1 X[f \mp f_s] + C_2 X[f \mp 2f_s] + C_3 X[f \mp 3f_s] \dots$$

Frequency domain view



Key: Its also a filter...
But with folding.

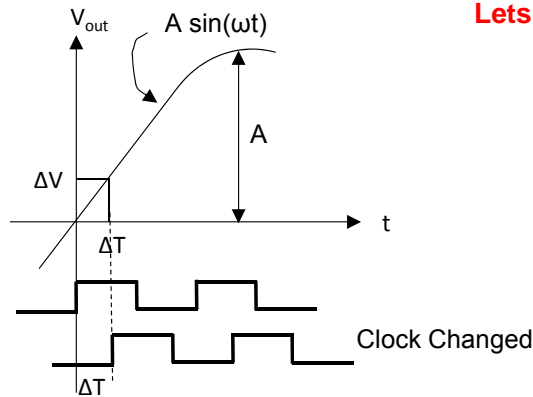
So now we need to make sure f_s farther than f_x .- more on adc lect.

Sampling inaccuracy – Jitter

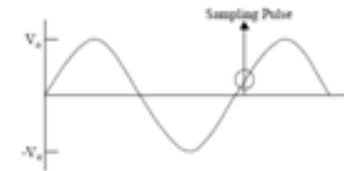
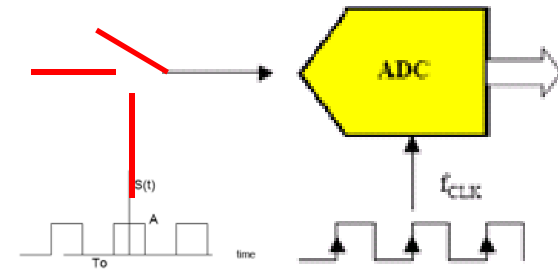
The TH is ideal but the clock is changing...

Jitter error – what will it do to a converter? – name it : Apparatus Error

Lets say the input is a pure sine wave



Sampling Time Uncertainty



$\Delta T = \text{Jitter} = t_{\text{jitter}}$
 $A = \text{Signal Amplitude} = A \sin(\omega t)$

Search for Max ΔV , but $\Delta V \leq 1\text{LSB}$

$$\left. \frac{\Delta V}{\Delta T} \right|_{\max} = \left. \frac{dV}{dT} \right|_{t=0} = A\omega \cos \omega t = A\omega$$

But:

$$2A = \text{Converter Range} \rightarrow \text{LSB} = \frac{2A}{2^n - 1}$$

Find t_{jitter} that don't let it cause more than an LSB or error.. (actually I use $\frac{1}{4}$).

Jitter effect: calculation

$$\left. \frac{\Delta V}{\Delta T} \right|_{max} = A\omega$$

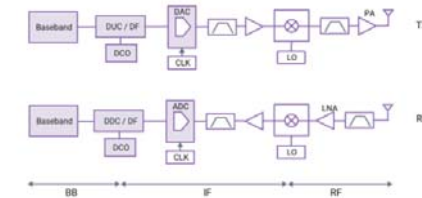
$$\Delta T \Big|_{max} = \frac{LSB \cdot 2}{\omega \cdot 2^n \cdot LSB} = \frac{1}{\pi f_{in} 2^n}$$

$\Delta T \Big|_{max}$ = Peak-to-Peak Clock Uncertainty

n=Bits	Δt_{max} [ps]
10	31
12	7.77
14	1.9
12	0.19

} $f_{in} = 10\text{MHz}$
 } $f_{in} = 400\text{MHz}$

This is ****Jitter..**** (depends on f input)



Key: Its worth case
Reality you need
phase noise...

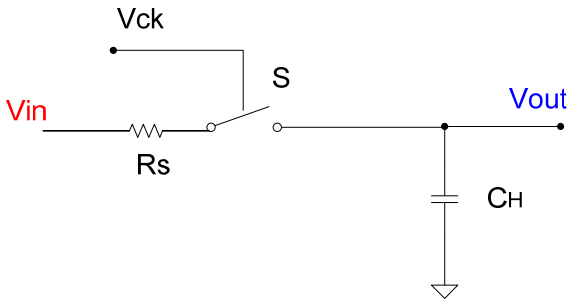
What adc jitter needed
for wifi-5G ?
3-4Gsp/s

WiFi/5G
coordinate on
unlicensed bands

53 e-15 ?

As for today, PLLs are $\approx 1\text{-}2\text{ps}$.. below 100fs is hard to build

Basic S/H, Signal BW – Large and small BW !



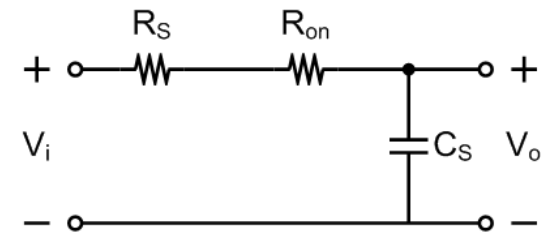
Simple model with source resistor

Small signal BW – Assuming we can charge the capacitor

$f_{-3db} = 1 / (2 \pi R_s C_H)$ – cont. see page 15

Rs can be the driver resistance, and the switch, can vary
 Ch- is load capacitance amplifier ? Comparator ? Wiring ?

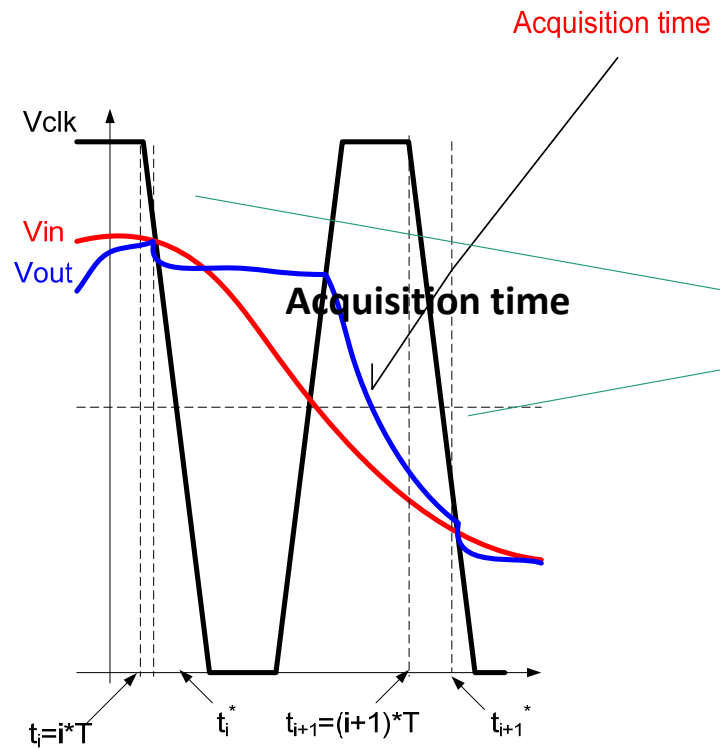
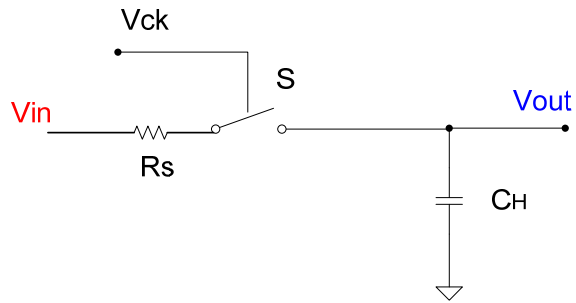
Why we care ? – to catch the signal ... acquisition. Time..
 If we don't catch it ?



$TBW = 1 / (R_s + R_{on}) C_s$

Professor Y. Chiu
 Fall 2012

Acquisition time



The problem the switch is the source and the clock is the gate

Remember the place of the two $-V_t$ makes an off region..

Example acquisition time

Acquisition: For a step input the response is

$$V_{out} = (dV) (1 - \exp(-t/R_s C_h))$$

I_{max} is at $t=0$ and it is $V_{max} = V_{in} - V_{out}$

$$I_{max} = (V_{max}) / R_s \rightarrow 50 \text{ ohm} / 0.5 \text{V} / 2 \text{pF} = 10 \text{mA}$$

Accuracy Vs. Acquisition time

$$1\% = 4.6 R_s C_h$$

$$0.1\% = 6.9 R_s C_h = 10 \text{ bit}$$

$$0.01\% = 9.2 R_s C_h = 1/10000 = 13.28 \text{ bit}$$

In reality the input is moving, BW limited, and it is not a step input

if the input is **current limited** then the output is slewing at a rate of $dV_{out} / dt = I_{in} / C_h$

Here we don't deal with R switch
or lump its maximum with R_s to be less than
50 ohm

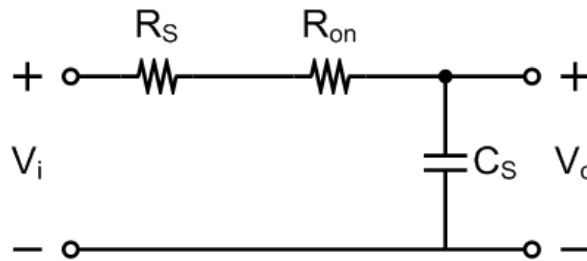
General form

Data Converters
EECT 7327

Sample-and-Hold

Professor Y. Chiu
Fall 2012

Acquisition Time (t_{acq})



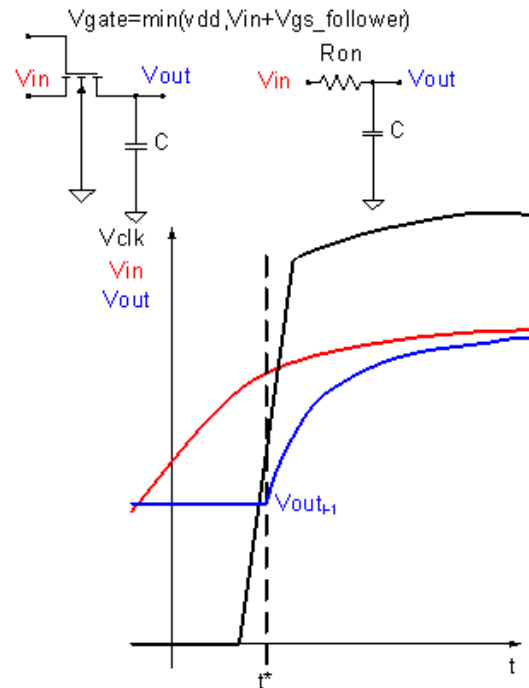
$$\tau = \frac{1}{\text{TBW}} = (R_S + R_{on})C_S$$

Accuracy	t_{acq}
1% (7b)	$\geq 5\tau$
0.1% (10b)	$\geq 7\tau$
0.01% (13b)	$\geq 9\tau$

$$R_{on} = \frac{1}{\mu C_{ox} \frac{W}{L} (V_{DD} - V_{th} - V_i)} = \frac{L^2}{\mu C_{ox} WL (V_{DD} - V_{th} - V_i)} = \frac{L^2}{\mu Q_{ch}}$$

Short L, thin t_{ox} , large W, large V_{ov} , and small V_i help reduce R_{on}

Complete form solution



Tracking/settling error calculation:

$$V_{in}(t) = V_{cm} + A \sin(2\pi f_{in}^s t)$$

$$V_{in}(t) = V_{out}(t) + R_{on} \cdot C \frac{\partial V_{out}}{\partial t} \quad t = t^* \Rightarrow V_{out} = V_{out_{i-1}} \cong V_{in} \left(t^* - \frac{1}{2f_{smp}} \right)$$

Forced solution:
$$V_{out}^f(t) = V_{cm} + \frac{A \sin[2\pi f_{in}^s t - \arctan(2\pi f_{in}^s R_{on} C)]}{\sqrt{1 + 4\pi^2 f_{in}^2 R_{on}^2 C^2}}$$

Homogenous solution:
$$V_{out}^h(t) = B \cdot e^{-\frac{t-t^*}{R_{on} C}}$$

Solution:
$$V_{out}(t) = V_{out}^h(t) + V_{out}^f(t)$$

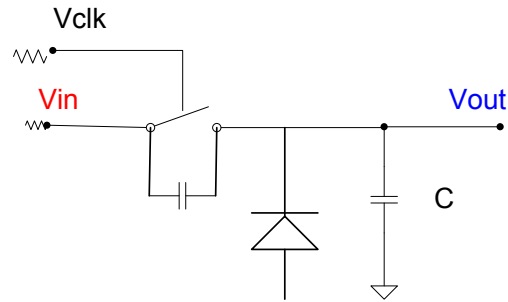
Set initial condition (determine B):

$$\begin{aligned}
 B &= V_{out_{i-1}} - V_{cm} - \frac{A \sin[2\pi f_{in}^s t^* - \arctan(2\pi f_{in}^s R_{on} C)]}{\sqrt{1 + 4\pi^2 f_{in}^2 R_{on}^2 C^2}} \cong \\
 &\cong \frac{A \sin \left[2\pi f_{in}^s \left(t^* - \frac{1}{2f_{smp}} \right) - \arctan(2\pi f_{in}^s R_{on} C) \right]}{\sqrt{1 + 4\pi^2 f_{in}^2 R_{on}^2 C^2}} - \frac{A \sin[2\pi f_{in}^s t^* - \arctan(2\pi f_{in}^s R_{on} C)]}{\sqrt{1 + 4\pi^2 f_{in}^2 R_{on}^2 C^2}} \\
 &= \frac{-2A}{\sqrt{1 + 4\pi^2 f_{in}^2 R_{on}^2 C^2}} \cos \left[2\pi f_{in}^s \left(t^* - \frac{1}{4f_{smp}} \right) - \arctan(2\pi f_{in}^s R_{on} C) \right] \sin \left(\frac{\pi f_{in}^s}{2f_{smp}} \right)
 \end{aligned}$$

fundamental performance limits

- Frequency domain transfer function
- Sample Jitter and clock jitter
- Acquisition Time, Sample BW
- Droop and Feed through ←
- KT/C noise
- Real Performance limits
- Charge Injections
- Capacitive noise from Supply
- PSRR
- Linearity

Droop Mode and Feed through- MOS Switch

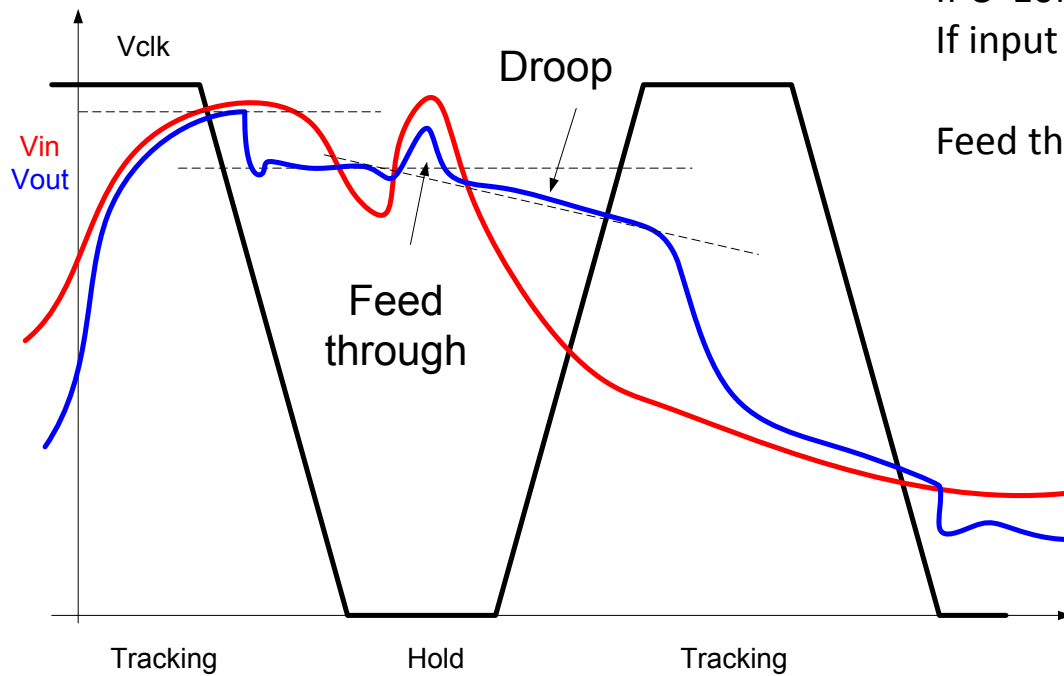


If $C=10\text{ff}$, $I_{\text{diode}}=20\text{fA}$, $C=100\text{fF}$

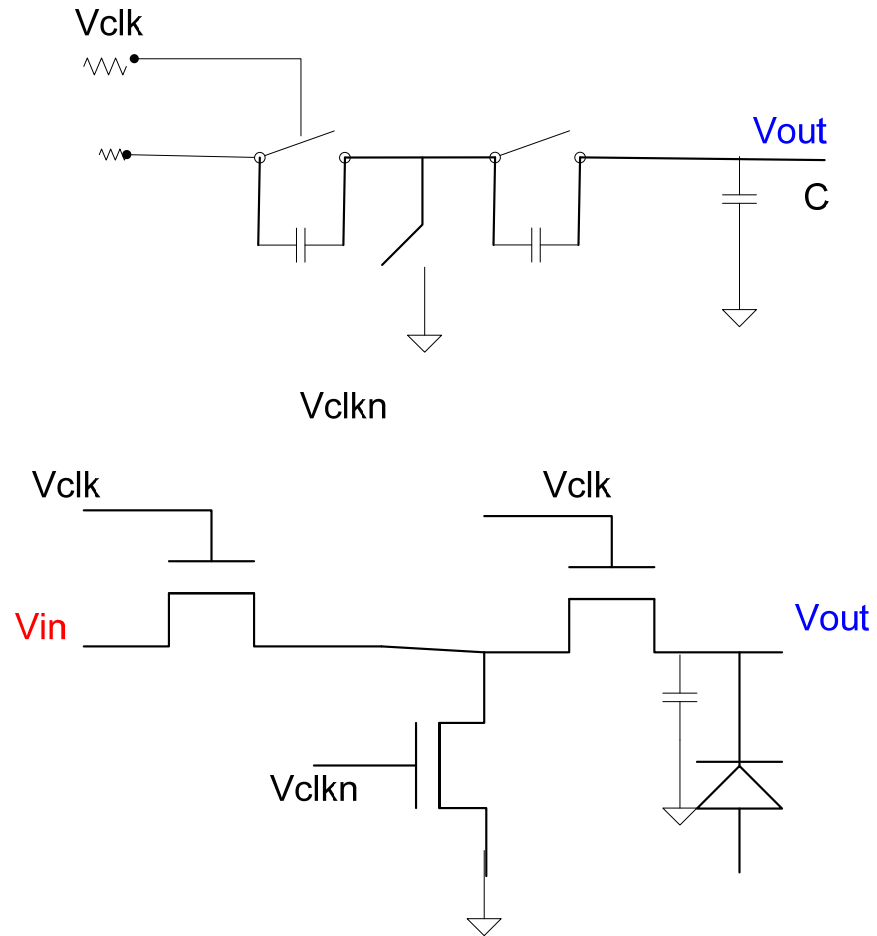
Drop by 1mv if, $(c/i)\text{dV}$, **off time=0.5ms**

If $C=10\text{ff}$, $I_{\text{diode}}=20\text{fA}$, $C=100\text{fF}$ (with diode)
 If input change 20mv during hold

Feed through = $"10/110" = 1.8\text{mV}$.

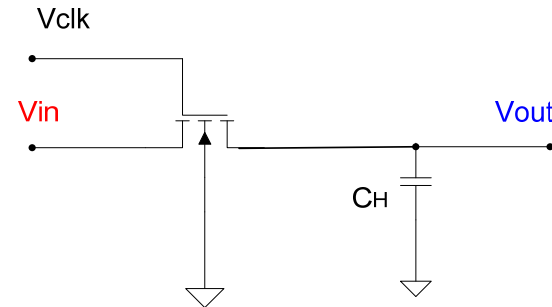


Improved feed-through problem



Cost: double the switch R

Part II : S/H MOS SWITCH Transistor as switch Basic Configuration:

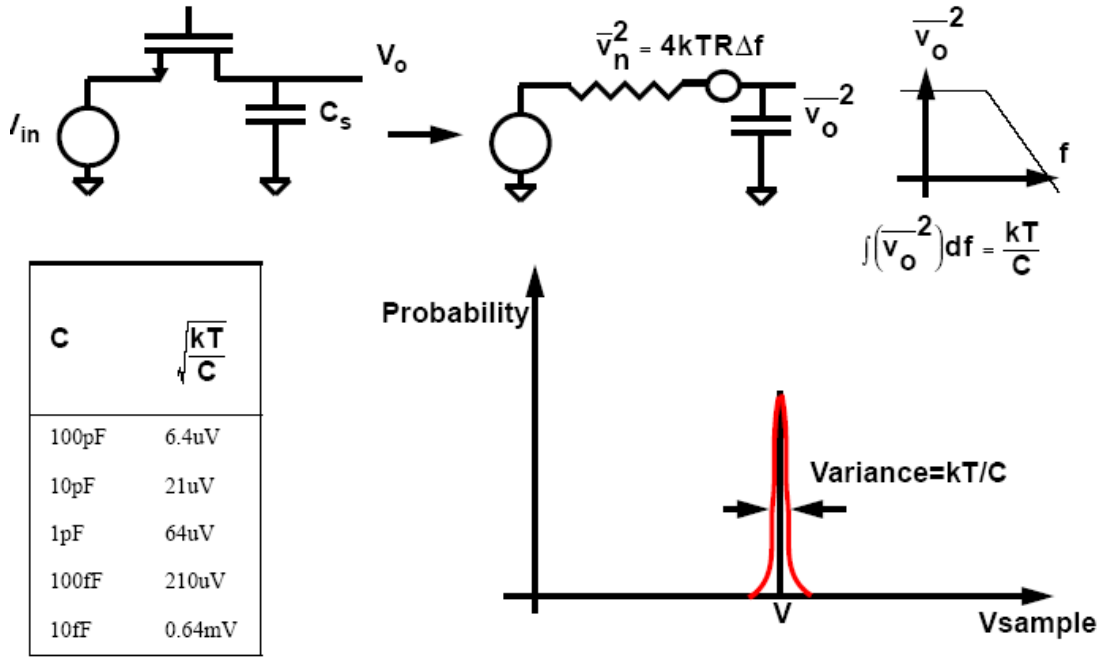


fundamental performance limits



KT/C noise
Real Performance limits
Charge Injections
Capacitive noise from Supply
PSRR
Linearity

kT/C Noise Limitation



Thermal noise:

$$\Delta V_{thermal}^2 = \frac{kT}{C}$$

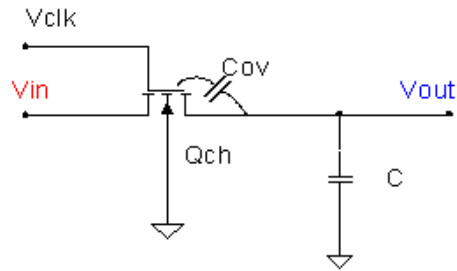
Key : Noise is determined by the hold capacitor.

Example:

0.2V sine wave and 100fF SNR= 56dB

$V_{Rms}/V_n = 141mv/210uV = 671 \rightarrow 56dB = 9bit$

Clock feed through

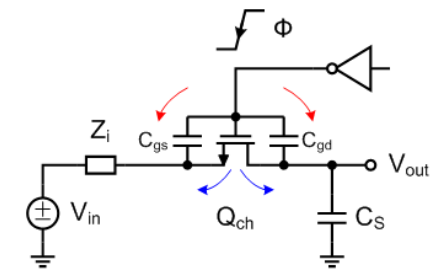


$$\Delta V_{\text{feedthrough}} \cong \Delta V_{\text{clk}} \frac{C_{ov}}{C} \cong -v_{dd} \frac{C_{ov}}{C}$$

Its large because Vclk has large swing

$$V_{out} \text{ change} = (C_{ov} / (C + C_{ov})) * V_{clk}$$

$C_{ov} \ll C$..but V_{clk} is large



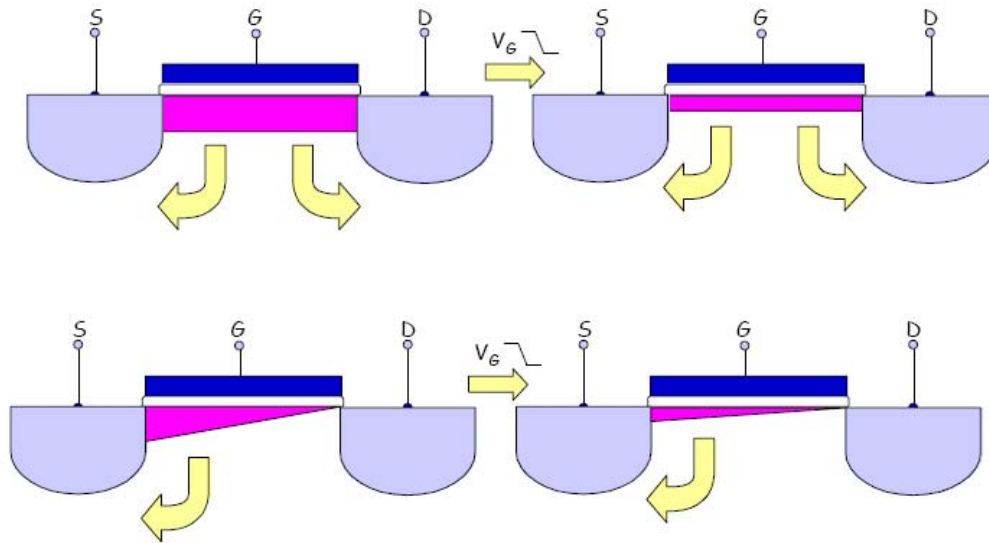
	Clock feedthrough (CF)
Fast turn-off	$\Delta V = -\frac{C_{gs}}{C_{gs} + C_S} V_{DD}$
Slow turn-off	$\Delta V = -\frac{C_{gs}}{C_{gs} + C_S} (V_{in} + V_{th})$

Professor Y. Chiu
Fall 2012

More exact

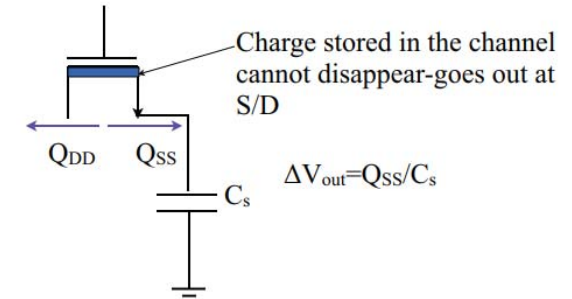
Charge injection from channel

Channel charge in (top) triode and (bottom) saturation



Problem : its function of v_{in} , v_{gate}

Charge Injection



Charge movement in the device..

1. If the switch is in triode : charge split

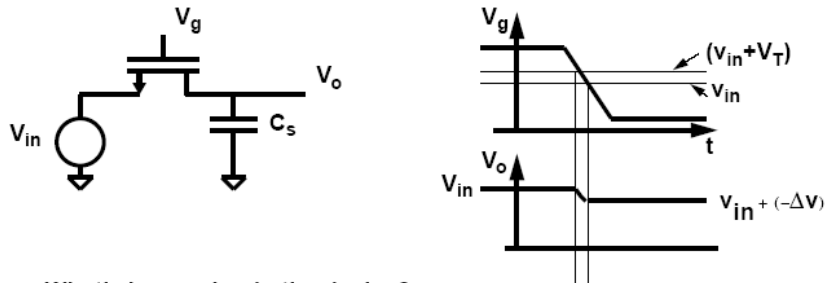
$$Q_{ch} = -WLC_{ox}(V_{GS} - V_T)$$

2. If the switch in sat all escapes to the source (nothing to the drain) Can we design SH based on sat switch?
3. In sat V_{drain} source cant reach 0

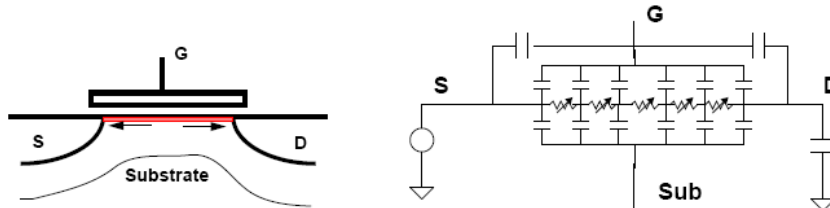
Page 27

Offset charge injection from channel

Sample/Hold Offset



What's happening in the device?



Limiting Case 1: Slow gate fall time, channel equilibrates

Limiting Case 2: Fast gate fall time, 1/2 of qc goes each way

Sample-and-Hold Basic Architectures

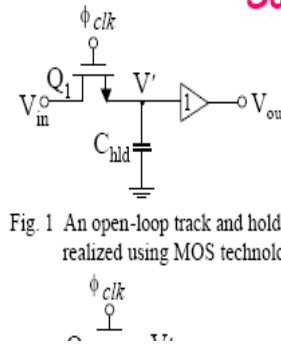


Fig. 1 An open-loop track and hold realized using MOS technology.

Analysis

$$\Delta Q_{Chld} = \frac{Q_{CH}}{2} = \frac{C_{OX}WL V_{eff-1}}{2}$$

where V_{eff-1} is given by

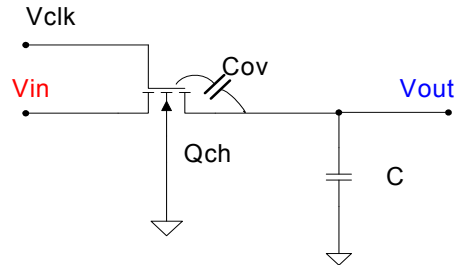
$$V_{eff-1} = V_{GS1} - V_m = V_{DD} - V_m - V_{in}$$

$$\Delta V' = \frac{\Delta Q_{C-hld}}{C_{hld}} = -\frac{C_{OX}WL V_{eff-1}}{2C_{hld}} = -\frac{C_{OX}WL(V_{DD} - V_m - V_{in})}{2C_{hld}}$$

Charge Injection (very simple model)
(Half the channel charge goes to C):

$$\Delta V_{charge} \cong \frac{Q_{ch}}{2C} \cong -\frac{Cox \cdot W \cdot L(V_{gs} - V_{th})}{2C} = -\frac{Cox \cdot W \cdot L(v_{dd} - V_{in}(t) - V_{th}(V_{in}(t)))}{2C}$$

Summary on those 3



$$\Delta V_{feedthrough} \cong \Delta V_{clk} \frac{C_{ov}}{C} \cong -v_{dd} \frac{C_{ov}}{C}$$

Charge Injection (very simple model)
 (Half the channel charge goes to C):

$$\Delta V_{charge} \cong \frac{Q_{ch}}{2C} \cong -\frac{C_{ox} \cdot W \cdot L (V_{gs} - V_{th})}{2C} = -\frac{C_{ox} \cdot W \cdot L (v_{dd} - V_{in}(t) - V_{th}(V_{in}(t)))}{2C}$$

Thermal noise:

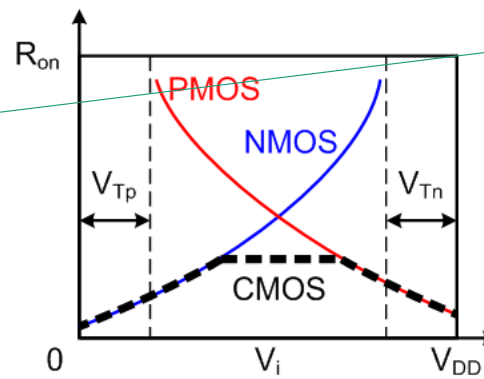
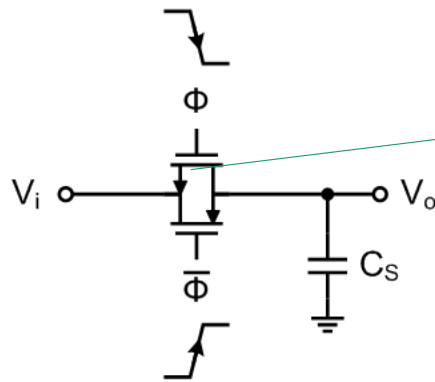
$$\Delta V_{thermal}^2 = \frac{kT}{C}$$

PRACTICAL DESIGN AND IMPLEMENTATIONS

CANCELLATION METHODS

Reduce Ron

CMOS Switch

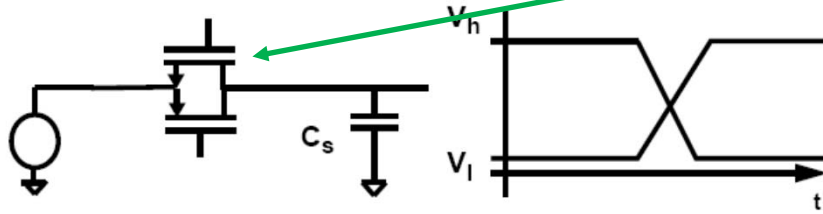


$$R_{on} = \frac{1}{\mu C_{ox} \frac{W}{L} (V_{DD} - V_{th} - V_i)} = \frac{L^2}{\mu C_{ox} W L (V_{DD} - V_{th} - V_i)} = \frac{L^2}{\mu Q_{ch}}$$

Short L, thin t_{ox} , large W, large V_{ov} , and small V_i help reduce R_{on}

- R_{on} still depends on V_{in} and is sensitive to N/P mismatch
- Large parasitic cap due to PMOS switch for symmetric R_{on}
- Clock rising/falling edge alignment

3. Complementary NMOS, PMOS



Assume fast case

$$\frac{1}{2}q_{CN} = \frac{1}{2}(V_H - |V_{TN}| - V_i)W_N L_N C_{oxN}$$

$$\frac{1}{2}q_{CP} = \frac{1}{2}(V_i - |V_{TP}| - V_L)W_P L_P C_{oxP}$$

$\Delta V = -V_{in}(1+\epsilon) + V_{OS}$ where:

$$\epsilon = \left(\frac{W_P L_P C_{oxP} + W_N L_N C_{oxN}}{C_L} \right)$$

$$V_{OS} = (V_{OSN} - V_{OSP}) \frac{C_{ol}}{C_L}$$

Key Point:

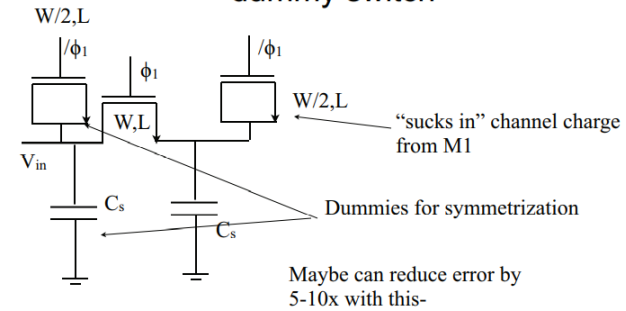
1. Offsets Partially Cancel

2. Gain errors ADD!!

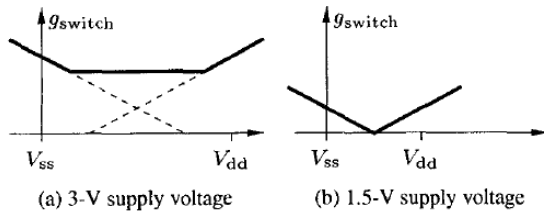
Do this

Or this

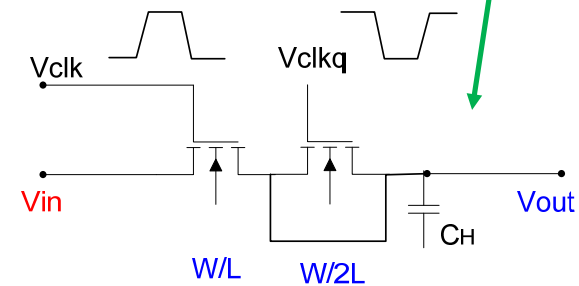
Charge injection mitigation(1) : dummy switch



EECS 240 Topic 16: Offset Cancellation © 2011 S.Gambini

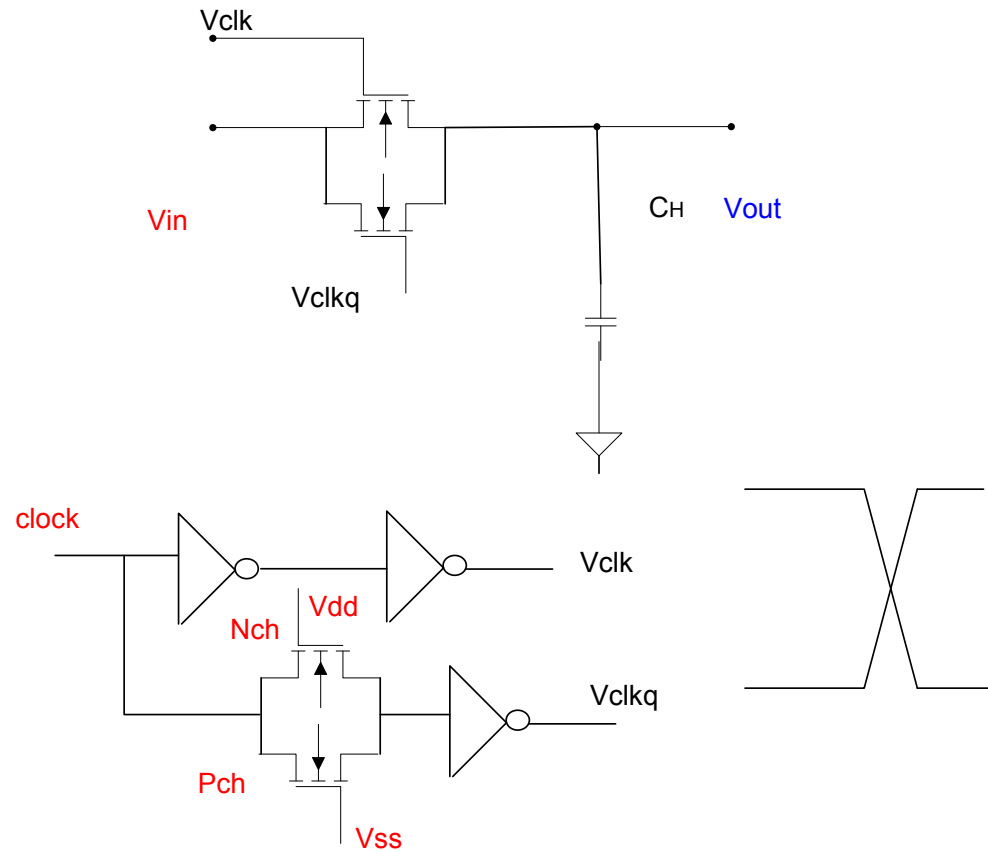


The Switch Ron improves



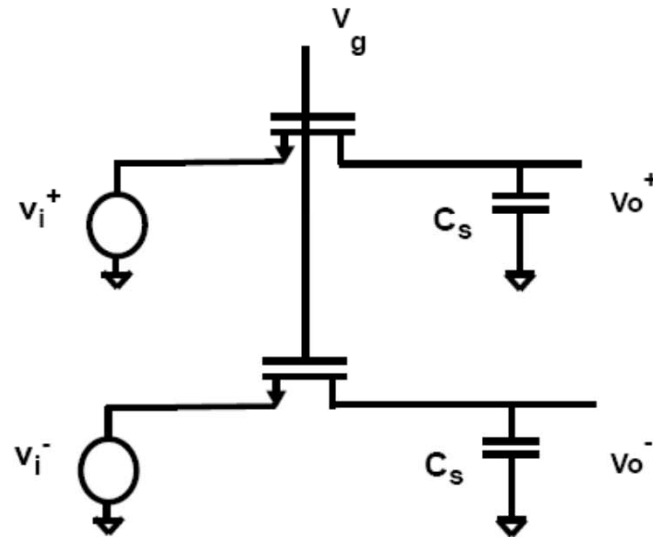
Dummy switch look for balancing clock fall and rise – not possible over all processes

Balance clock rise and fall time



But this is better

4. Get rid of offset- Go Differential



$$v_{o1} = v_{i1}(1 + \epsilon) + V_{os1}$$

$$v_{o2} = v_{i2}(1 + \epsilon) + V_{os2}$$

$$\Delta v_o = \Delta v_i(1 + \epsilon)$$

Even harmonics eliminated *to large degree*

practical circuits

**the biggest problem of all those
lies in distortions...**

How it all translate to ?

Distortion is the biggest issue

Distortion calculation and simulation

Unfortunately

$$R_{on} \approx R_0 \frac{V_{dd} - V_{th}}{V_{dd} - V_{th} - V_{in}} \longrightarrow \text{Distortion}$$

Bad mostly if $V_{in} > V_{dd} - V_{th}$ (NMOS) or $V_{in} < V_{th}$
 [Think of Pass Transistor Logic in 141/241]

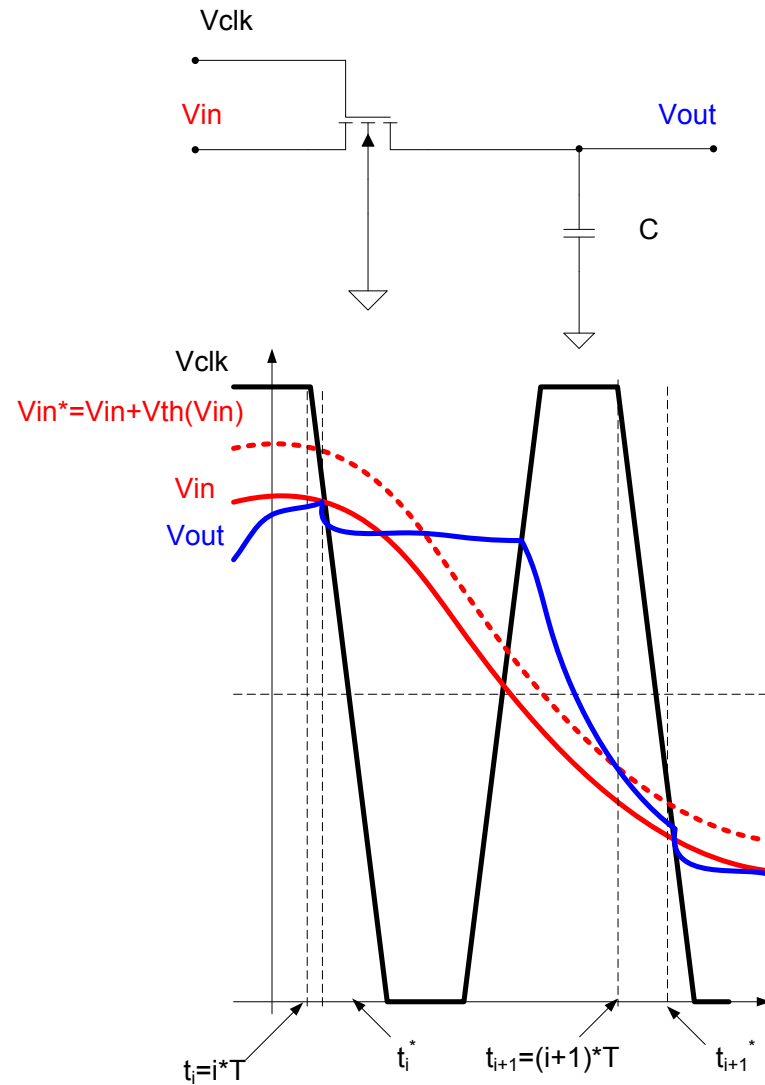
Constant V_{in} $V_{out} \approx V_{in} \left(1 - e^{-\frac{T_s}{2R_0C} \left(1 - \frac{V_{in}}{V_{dd} - V_{th}} \right)} \right)$

Remember competing effects large w/l to reduce Ron but charge injection grow as w&l

Lets combine all errors that related to input or output they all leads to non linearities...

- 1) **Do first pss sim- its fast and will let you know if the switch impedance is ok**
 you are lucky to get 80dB for 5GHz
- 1) **Then do fft on the results output- if bad either start taking vare of all issues**
- 2) **Optimize base in 1, 2 :Size, devices, use differentially, p and n in parallel**
- 3) **Then if not meet spec(fft) .. go to gate boosting..**

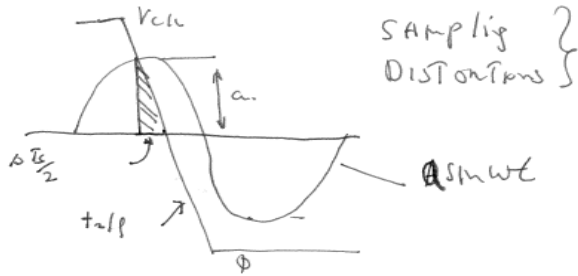
Aperture time accuracy - Pictorial view



The time when hold start is not the same on time

Distortion due to sampling time (apparatus time accuracy) calculations

Single mode



$$\Delta T = \frac{\Delta f_s}{2} = \left(\frac{a}{V_{clk}} \right) t_{rise}$$

$t_{rise} \Rightarrow$ Very Small
 $\omega \sin \omega t \ll \frac{1}{\Delta T}$

IF Input $V_{in} = a \sin \omega t$

$$\Delta T = \left(\frac{a}{V_{clk}} \right) t_{rise} \cdot \sin \omega t =$$

$$V_{out} = a \sin \omega (t + \Delta T) = a \sin \omega \left(t + \frac{a}{V_{clk}} t_{rise} \sin \omega t \right)$$

$$= a \sin \omega t + \omega \Delta T \cos \omega t \sin \omega t$$

$$= \underbrace{\frac{a}{2} \omega \Delta T}_{DC} + \underbrace{a \sin \omega t}_{Signal} + \underbrace{\frac{a}{2} \omega \Delta T \sin 2\omega t}_{H_2}$$

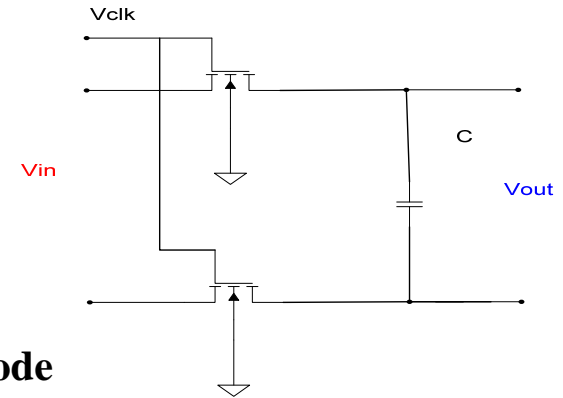
$$H_2 = \frac{\omega \Delta T}{2} = \frac{a}{2 V_{clk}} t_{rise}$$

can always be removed
diff!

100ps, $V_{clk} = 1.2V$ $a = 0.2V$ $f_{in} = 100MHz$

$H_2 = -45dB$ ←

Diff. mode



$$\left. \begin{aligned} V_{out}^+ &= a \sin \omega [t + \Delta T \sin \omega t] \\ V_{out}^- &= -a \sin \omega [t - \Delta T \sin \omega t] \end{aligned} \right\} R_1 = R_2$$

$$V_{out} = [V_{out}^+ - V_{out}^-] = a \sin \omega [t + \Delta T \sin \omega t] + a \sin \omega [t - \Delta T \sin \omega t]$$

$H_2 = 0$ IF $R_1 = R_2$

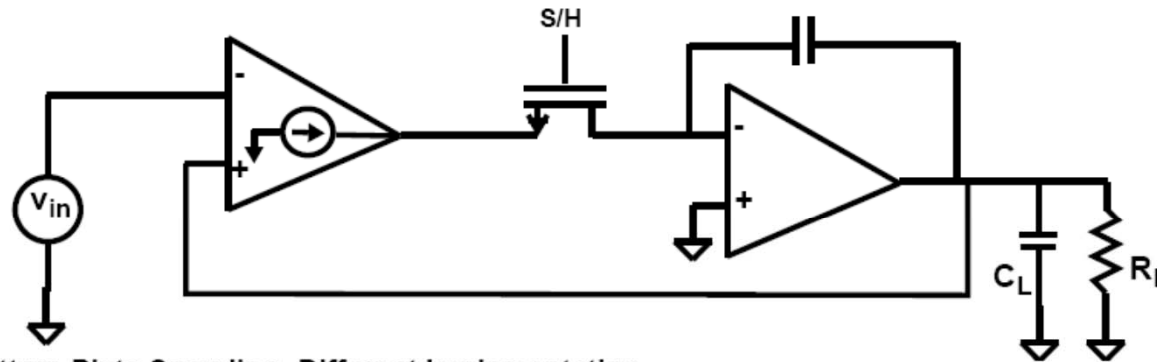
$H_3 \rightarrow$ how EXISTS $H_3 = \frac{1}{8} \omega^2 \Delta T^2$

Example.
 $= \frac{\pi^2}{2} \left(\frac{a}{V_{clk}} \right)^2 (f_{sig} \cdot t_{rise})^2 = -97dB$

IF $R_1 \neq R_2 \sim 70!$

circuits

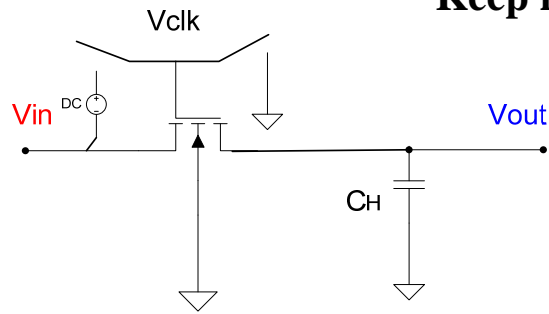
Example: Wooley JSC 12-89, Stafford JSC 12/74



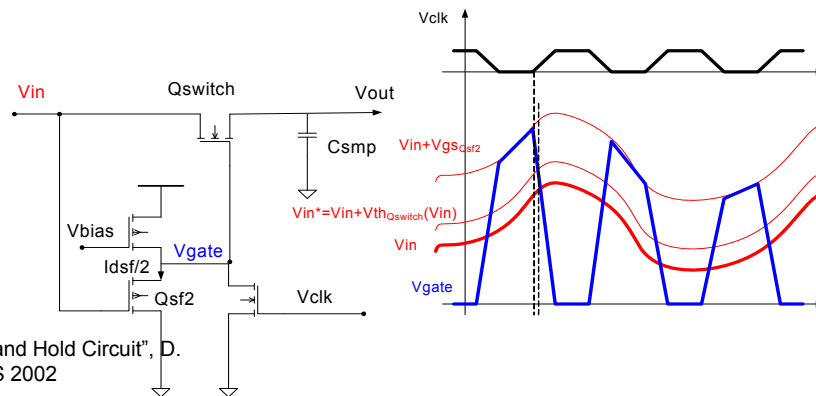
- Bottom-Plate Sampling- Different Implementation
- Output amp always active and valid
- Widely used in building blocks
- Disadvantage- Sample Mode Bandwidth limited by active devices
- Disadvantage- Offset, Noise limited by Amps

LINEARIZATION

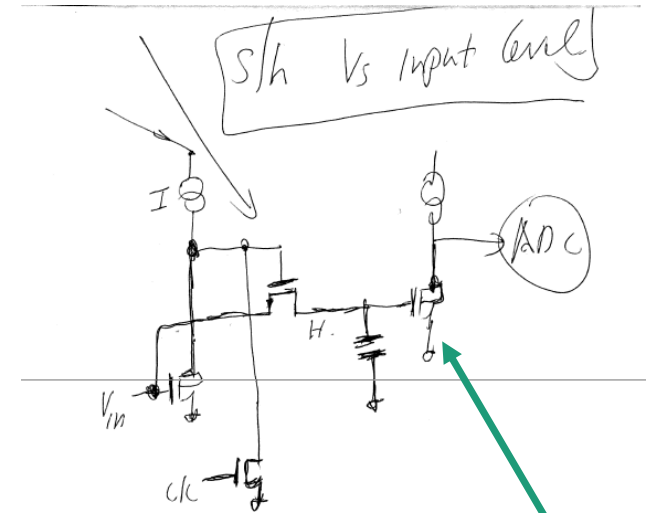
Keep resistance constant



Option 1:



“A 1GHz Linearized CMOS Track-and Hold Circuit”, D. Jakonis, C. Svensson, IEEE ISCAS 2002

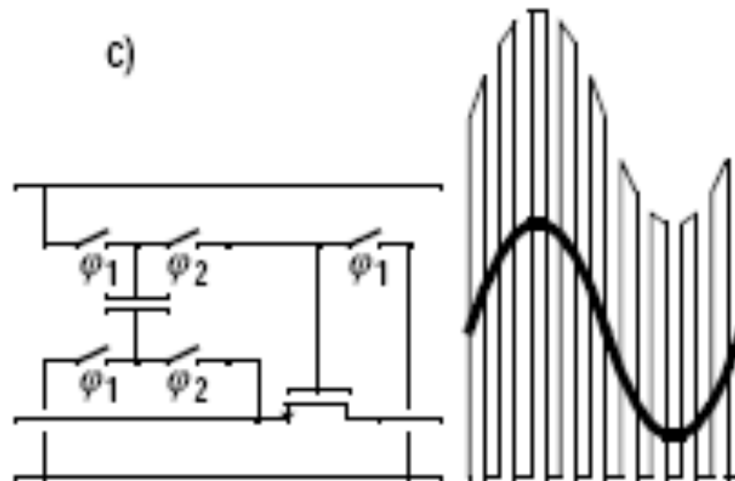


Need to include buffer

Can limit distortion +65-75 dB

Boot strapping

Option 2:



Abo and grey)

And the linearity at high speed (1Ghz) is a problem

For both the S/H and the buffer – No time for feedback opamps – Levels shifter are preferable

Basic Boosted Switch Configurations

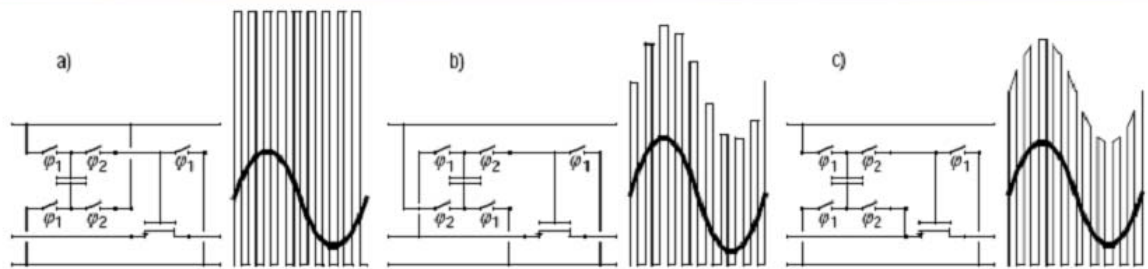


Fig. 7. Various Clock-Boosting techniques to operate switch over full supply range.

- a) Boosting the clock to $2x V_{dd}$
- Improved R_{on} (faster settling)
 - Signal dependent settling
 - Constant clock feed-through

- b) Boosting the clock to $V_{dd} + V_{in}$
- Improved R_{on} (faster settling)
 - Almost signal independent settling
 - Signal dependent clock feed-through
 - Input signal is loaded by boost cap during hold time

- c) Boosting the clock to $V_{in} + V_{dd}$
- Improved R_{on} (faster settling)
 - Signal independent settling
 - Signal dependent clock feed-through
 - Input signal is loaded by boost cap during track time

"Analog Design in Deep Sub-Micron CMOS" Klaas BultA, ESSCIRC, 2000

END
lecture 04